

# RJH60F4DPK

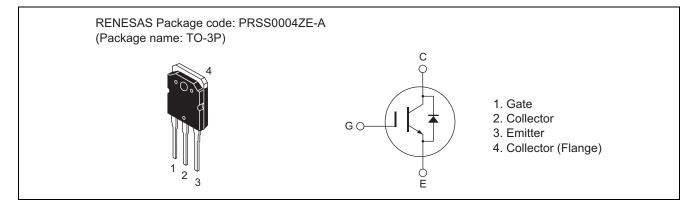
# Silicon N Channel IGBT High Speed Power Switching

REJ03G1835-0100 Rev.1.00 Oct 13, 2009

### **Features**

- High speed switching
- Low on-state voltage
- Fast recovery diode

### **Outline**



# **Absolute Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

Item		Symbol Ratings		Unit
Collector to emitter voltage		V <sub>CES</sub>	600	V
Gate to emitter voltage		V <sub>GES</sub>	±30	V
Collector current	Tc = 25 °C	I <sub>C</sub> Note1	60	Α
	Tc = 100 °C	I <sub>C</sub> Note1	30	Α
Collector peak current		ic(peak) Note1	120	Α
Collector to emitter diode forward peak current		i <sub>DF</sub> (peak) Note2	100	Α
Collector dissipation		Pc	235.8	W
Junction to case thermal impedance		θј-с	0.53	°C/W
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. Pulse width limited by safe operating area.

2.  $PW \le 5 \mu s$ , duty cycle  $\le 1\%$ 

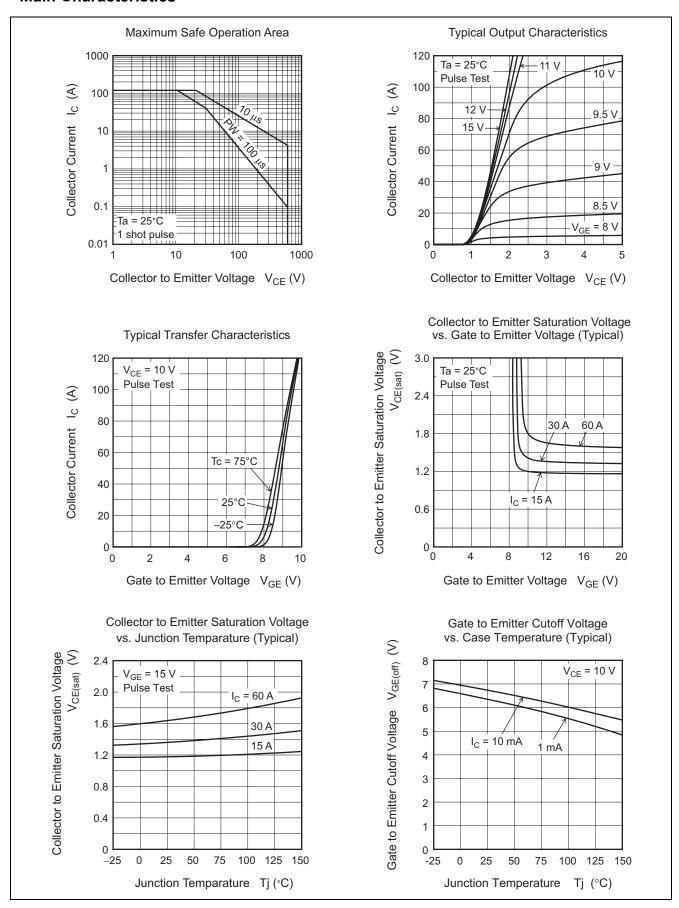
# **Electrical Characteristics**

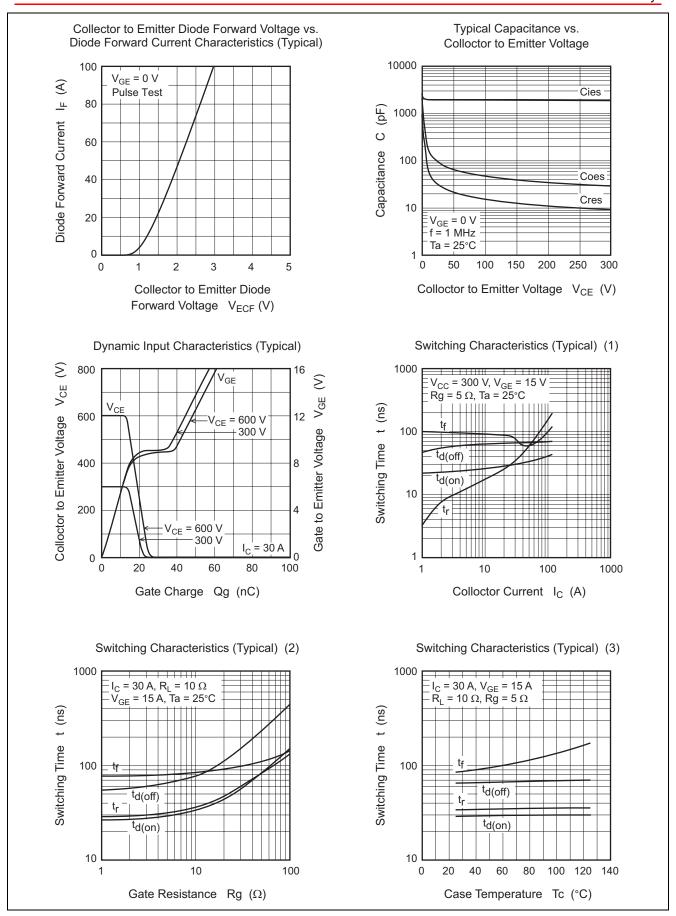
 $(Tj = 25^{\circ}C)$ 

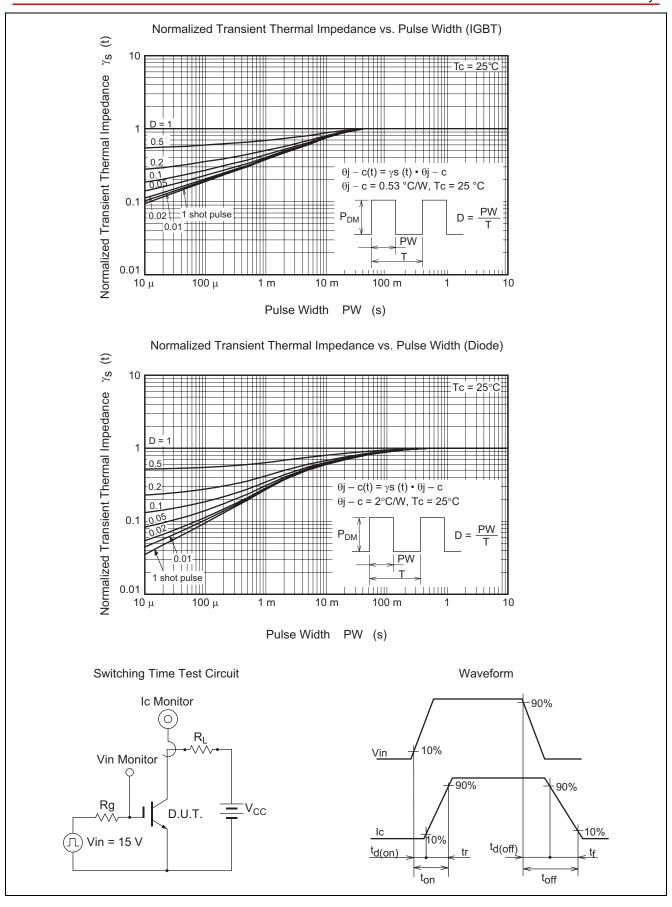
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current	I <sub>CES</sub>	_	_	100	μΑ	V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0
Gate to emitter leak current	I <sub>GES</sub>	_	_	±1	μΑ	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4	_	8	V	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1 mA
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	1.4	1.82	V	$I_C = 30 \text{ A}, V_{GE} = 15 \text{V}^{\text{Note3}}$
	V <sub>CE(sat)</sub>	_	1.7	_	V	I <sub>C</sub> = 60 A, V <sub>GE</sub> = 15V Note3
Input capacitance	Cies	_	1945	_	pF	V <sub>CE</sub> = 25 V
Output capacitance	Coes	_	93	_	pF	V <sub>GE</sub> = 0 V
Reverse transfer capacitance	Cres	_	33	_	pF	f = 1 MHz
Switching time	t <sub>d(on)</sub>	_	30	_	ns	I <sub>C</sub> = 30 A, Resistive Load
	t <sub>r</sub>	_	32	_	ns	V <sub>CC</sub> = 300V
	$t_{d(off)}$	_	65	_	ns	V <sub>GE</sub> = 15V
	t <sub>f</sub>	_	80	_	ns	$Rg = 5 \Omega^{Note3}$
C-E diode forward voltage	V <sub>ECF1</sub>	_	1.6	2.1	V	I <sub>F</sub> = 20 A <sup>Note3</sup>
	V <sub>ECF2</sub>	_	1.8	_	V	I <sub>F</sub> = 40 A <sup>Note3</sup>
C-E diode reverse recovery time	t <sub>rr</sub>	_	140	_	ns	I <sub>F</sub> = 20 A
						$di_F/dt = 100 A/\mu s$

Notes: 3. Pulse test

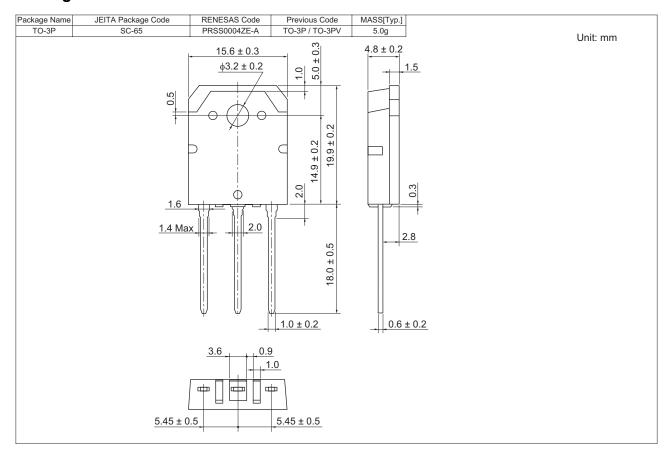
## **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJH60F4DPK-00-T0	360 pcs	Box (Tube)

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